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Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.25GHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	Cryptography
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8536eavjatha

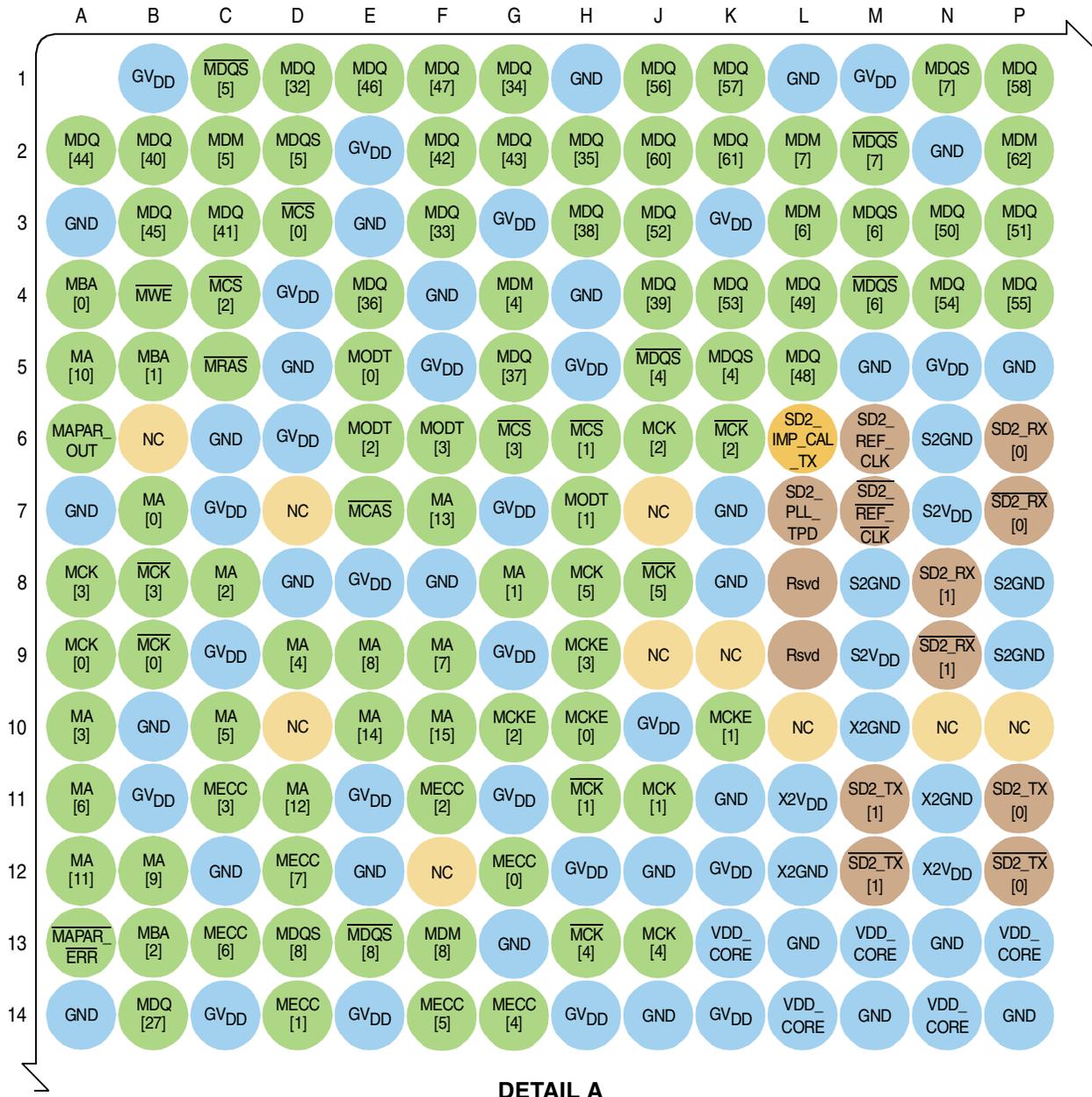


Figure 3. Chip Pin Map Detail A

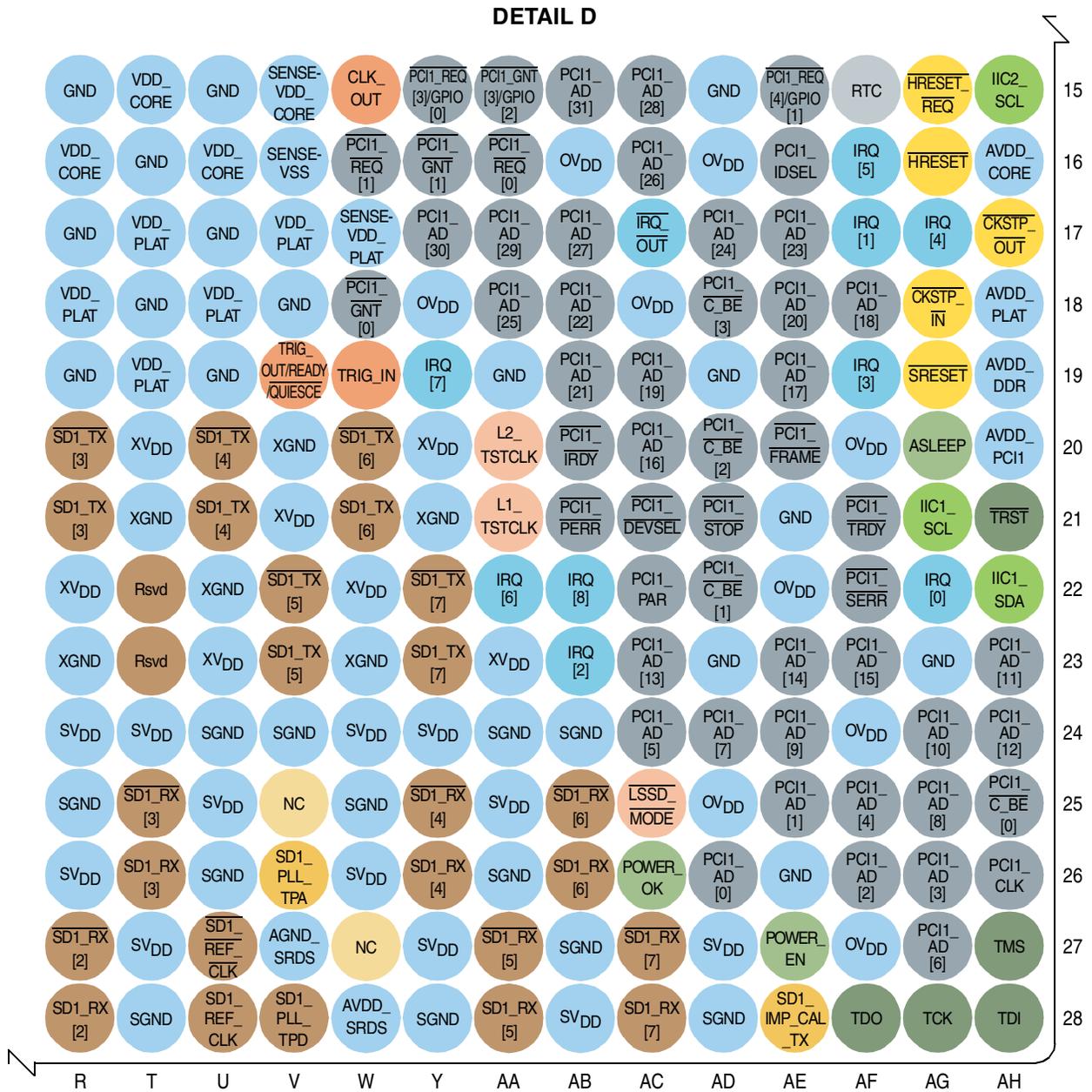


Figure 6. Chip Pin Map Detail D

This table provides the pin-out listing for the 783 FC-PBGA package.

Table 1. Pinout Listing

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
PCI					
PCI1_AD[31:0]	Muxed Address / data	AB15,Y17,AA17,AC15, AB17,AC16,AA18, AD17,AE17,AB18, AB19,AE18,AC19, AF18,AE19,AC20, AF23,AE23,AC23, AH24,AH23,AG24, AE24,AG25,AD24, AG27,AC24,AF25, AG26,AF26,AE25, AD26	I/O	OV _{DD}	—
PCI1_C_BE[3:0]	Command/Byte Enable	AD18, AD20,AD22, AH25	I/O	OV _{DD}	29
PCI1_PAR	Parity	AC22	I/O	OV _{DD}	29
PCI1_FRAME	Frame	AE20	I/O	OV _{DD}	2,29
PCI1_TRDY	Target Ready	AF21	I/O	OV _{DD}	2,29
PCI1_IRDY	Initiator Ready	AB20	I/O	OV _{DD}	2,29
PCI1_STOP	Stop	AD21	I/O	OV _{DD}	2,29
PCI1_DEVSEL	Device Select	AC21	I/O	OV _{DD}	2,29
PCI1_IDSEL	Init Device Select	AE16	I	OV _{DD}	29
PCI1_PERR	Parity Error	AB21	I/O	OV _{DD}	2,29
PCI1_SERR	System Error	AF22	I/O	OV _{DD}	2,4,29
PCI1_REQ[4:3]/GPIO[1:0]	Request	AE15,Y15	I	OV _{DD}	—
PCI1_REQ[2:1]	Request	AF13,W16	I	OV _{DD}	29
PCI1_REQ[0]	Request	AA16	I/O	OV _{DD}	29
PCI1_GNT[4:3]/GPIO[3:2]	Grant	AC14, AA15	O	OV _{DD}	
PCI1_GNT[2:1]	Grant	AF14,Y16	O	OV _{DD}	5,9,25,29
PCI1_GNT[0]	Grant	W18	I/O	OV _{DD}	29
PCI1_CLK	PCI Clock	AH26	I	OV _{DD}	29

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
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Notes:

1. All multiplexed signals may be listed only once and may not re-occur.
2. Recommend a weak pull-up resistor (2–10 K Ω) be placed on this pin to OV_{DD} .
3. This pin must always be pulled-high.
4. This pin is an open drain signal.
5. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-k Ω pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pullup or active driver is needed.
6. Treat these pins as no connects (NC) unless using debug address functionality.
7. The value of LA[28:31] during reset sets the CCB clock to SYSCLK PLL ratio. These pins require 4.7-k Ω pull-up or pull-down resistors. See [Section 22.2, “CCB/SYSCLK PLL Ratio.”](#)
8. The value of LALE, LGPL2 and LBCTL at reset set the e500 core clock to CCB Clock PLL ratio. These pins require 4.7-k Ω pull-up or pull-down resistors. See the [Section 22.3, “e500 Core PLL Ratio.”](#)
9. Functionally, this pin is an output, but structurally it is an I/O because it either samples configuration input during reset or because it has other manufacturing test functions. This pin will therefore be described as an I/O for boundary scan.
10. For proper state of these signals during reset, UART_SOUT[1] must be pulled down to GND through a resistor. UART_SOUT[0] can be pulled up or left without a resistor. However, if there is any device on the net which might pull down the value of the net at reset, then a pullup is needed on UART_SOUT[0].
11. This output is actively driven during reset rather than being three-stated during reset.
12. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
13. These pins are connected to the $V_{DD_CORE}/V_{DD_PLAT}/GND$ planes internally and may be used by the core power supply to improve tracking and regulation.
15. These pins have other manufacturing or debug test functions. It's recommended to add both pull-up resistor pads to OVDD and pull-down resistor pads to GND on board to support future debug testing when needed.
16. If this pin is connected to a device that pulls down during reset, an external pull-up is required to drive this pin to a safe state during reset.
17. This pin is only an output in FIFO mode when used as Rx Flow Control.
18. Do not connect.
19. These must be pulled up (100 Ω - 1 k Ω) to OVDD.
20. Independent supplies derived from board VDD.
21. Recommend a pull-up resistor (1 K Ω) be placed on this pin to OV_{DD} .
22. The following pins must NOT be pulled down during power-on reset: MDVAL, UART_SOUT[0], EC_MDC, TSEC1_TXD[3], TSEC3_TXD[7], HRESET_REQ, TRIG_OUT/READY/QUIESCE, MSRCID[2:4], ASLEEP.
23. This pin requires an external 4.7-k Ω pull-down resistor to prevent PHY from seeing a valid Transmit Enable before it is actively driven.
24. General-Purpose POR configuration of user system.

Table 3. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD_CORE}	$1.0 \pm 50 \text{ mV}$	V	—
Platform supply voltage		V_{DD_PLAT}	$1.0 \pm 50 \text{ mV}$	V	—
PLL core supply voltage		AV_{DD_CORE}	$1.0 \pm 50 \text{ mV}$	V	2
PLL other supply voltage		AV_{DD}	$1.0 \pm 50 \text{ mV}$	V	2
Core power supply for SerDes transceivers		SV_{DD}	$1.0 \pm 50 \text{ mV}$	V	—
Pad power supply for SerDes transceivers and PCI Express		XV_{DD}	$1.0 \pm 50 \text{ mV}$	V	—
DDR SDRAM Controller I/O supply voltage	DDR2 SDRAM Interface	GV_{DD}	$1.8 \text{ V} \pm 90 \text{ mV}$	V	3
	DDR3 SDRAM Interface		$1.5 \text{ V} \pm 75 \text{ mV}$		
Three-speed Ethernet I/O voltage		LV_{DD} (eTSEC1)	$3.3 \text{ V} \pm 165 \text{ mV}$ $2.5 \text{ V} \pm 125 \text{ mV}$	V	5
		TV_{DD} (eTSEC3)	$3.3 \text{ V} \pm 165 \text{ mV}$ $2.5 \text{ V} \pm 125 \text{ mV}$		
PCI, DUART, system control and power management, I ² C, USB, eSDHC, eSPI and JTAG I/O voltage, MII management voltage		OV_{DD}	$3.3 \text{ V} \pm 165 \text{ mV}$	V	4
Local bus I/O voltage		BV_{DD}	$3.3 \text{ V} \pm 165 \text{ mV}$ $2.5 \text{ V} \pm 125 \text{ mV}$ $1.8 \text{ V} \pm 90 \text{ mV}$	V	—
Input voltage	DDR2 and DDR3 SDRAM Interface signals	MV_{IN}	GND to GV_{DD}	V	3
	DDR2 and DDR3 SDRAM Interface reference	MV_{REF}	$GV_{DD}/2 \pm 1\%$	V	—
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	5
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, Local bus, DUART, SYSCLK, system control and power management, I ² C, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	4
Operating Temperature range	Commercial	T_A T_J	$T_A = 0 \text{ (min) to } T_J = 90 \text{ (max)}$	°C	6
	Industrial standard temperature range Extended temperature range		$T_A = 0 \text{ (min) to } T_J = 105 \text{ (max)}$		
			$T_A = -40 \text{ (min) to } T_J = 105 \text{ (max)}$		

Notes:

- This voltage is the input to the filter discussed in [Section 3.2.1, “PLL Power Supply Filtering,”](#) and not necessarily the voltage at the AVDD pin, which may be reduced from VDD by the filter.
- Caution:** MVIN must not exceed GVDD by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- Caution:** OVIN must not exceed OVDD by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- Caution:** L/TVIN must not exceed L/TVDD by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- Minimum temperature is specified with T_A ; maximum temperature is specified with T_J .

2.4.4 eTSEC Gigabit Reference Clock Timing

This table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the chip.

Table 8. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK rise and fall time LV _{DD} , TV _{DD} = 2.5V LV _{DD} , TV _{DD} = 3.3V	t_{G125R}/t_{G125F}	—	—	0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125L}	45 47	—	55 53	%	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5V and 2.0V for L/TVDD=2.5V, and from 0.6 and 2.7V for L/TVDD=3.3V at 0.6 V and 2.7 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See [Section 2.9.2.6, “RGMII and RTBI AC Timing Specifications,”](#) for duty cycle for 10Base-T and 100Base-T reference clock.

2.4.5 DDR Clock Timing

This table provides the DDR clock (DDRCLK) AC timing specifications for the chip.

Table 9. DDRCLK AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3V ± 5%.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
DDRCLK frequency	f_{DDRCLK}	66	—	166	MHz	1
DDRCLK cycle time	t_{DDRCLK}	6.0	—	15.15	ns	—
DDRCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
DDRCLK duty cycle	t_{KHK}/t_{DDRCLK}	40	—	60	%	—
DDRCLK jitter	—	—	—	+/- 150	ps	3, 4

Notes:

1. **Caution:** The DDR complex clock to DDRCLK ratio settings must be chosen such that the resulting DDR complex clock frequency does not exceed the maximum or minimum operating frequencies. See [Section 2.23.4, “DDR/DDRCLK PLL Ratio,”](#) for ratio settings.
2. Rise and fall times for DDRCLK are measured at 0.6 V and 2.7 V.
3. The DDRCLK driver's closed loop jitter bandwidth should be <500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track DDRCLK drivers with the specified jitter.
4. For spread spectrum clocking, guidelines are +0% to -1% down spread at a modulation rate between 20 kHz and 60 kHz on DDRCLK.

Electrical Characteristics

This figure shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

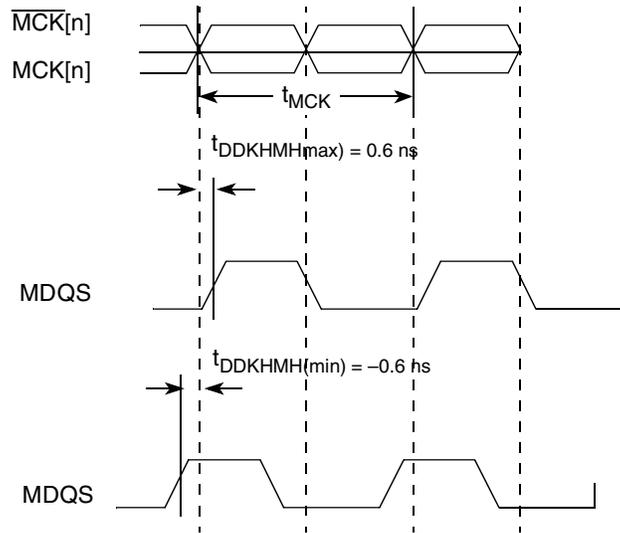


Figure 9. Timing Diagram for t_{DDKHMH}

This figure shows the DDR SDRAM output timing diagram.

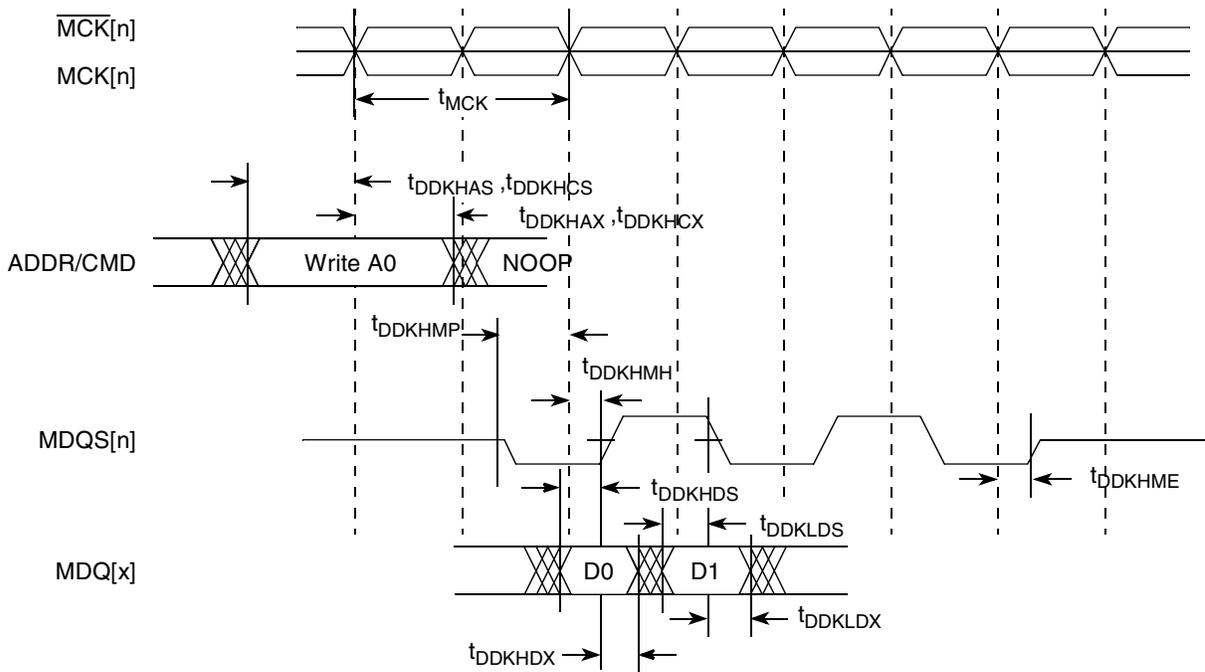


Figure 10. DDR SDRAM Output Timing Diagram

Table 21. SPI AC Timing Specifications¹ (continued)

Characteristic	Symbol ²	Min	Max	Unit	Note
SPI_CS outputs—Master data delay	$t_{\text{NIKH OV2}}$	—	6.0	ns	—
SPI inputs—Master data input setup time	t_{NIIVKH}	5	—	ns	—
SPI inputs—Master data input hold time	t_{NIIXKH}	0	—	ns	—

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{\text{NIKH OV}}$ symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).
3. SPCOM[RxDelay] is set to 0.
4. SPCOM[RxDelay] is set to 1.

This figure provides the AC test load for the SPI.

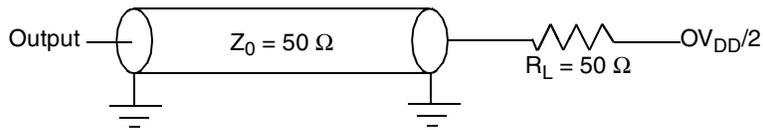
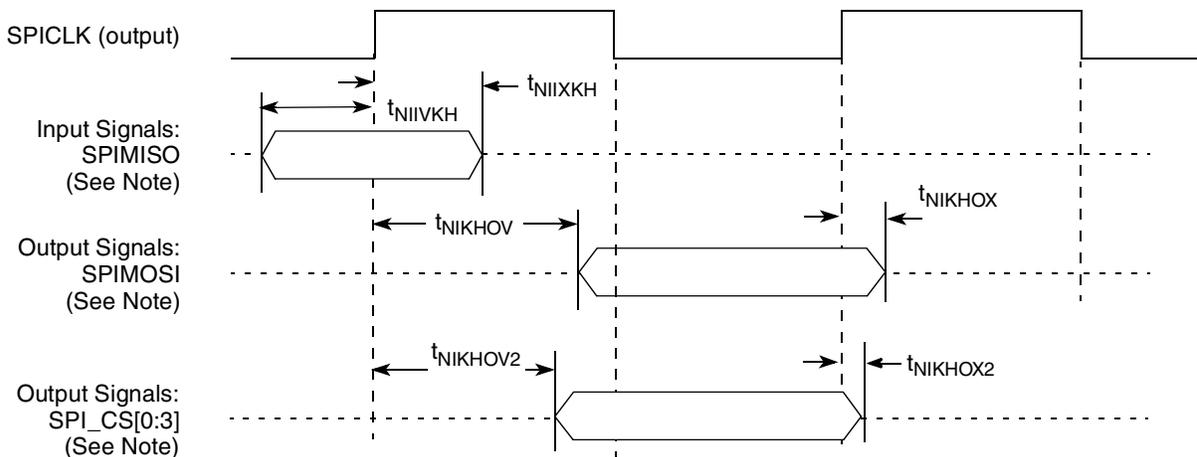


Figure 12. SPI AC Test Load

This figure represents the AC timing from Table 21. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.



Note: The clock edge is selectable on SPI.

Figure 13. SPI AC Timing in Master mode (Internal Clock) Diagram

Electrical Characteristics

A timing diagram for TBI receive appears in the following figure.

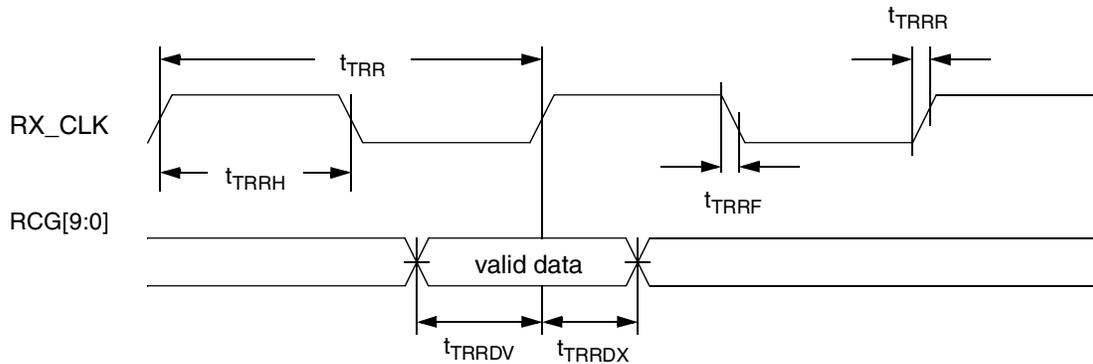


Figure 24. TBI Single-Clock Mode Receive AC Timing Diagram

2.9.2.6 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

Table 35. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of $2.5\text{ V} \pm 5\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT_TX}	-500	0	500	ps
Data to clock input skew (at receiver) ²	t_{SKRGT_RX}	1.0	—	2.8	ns
Clock period duration ³	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000BASE-T ⁴	t_{RGTH}/t_{RGT}	45	—	55	%
Duty cycle for 10BASE-T and 100BASE-TX ^{3, 4}	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (20%–80%)	t_{RGTF}	—	—	0.75	ns

Notes:

- Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
- This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
- For 10 and 100 Mbps, t_{RGT} scales to $400\text{ ns} \pm 40\text{ ns}$ and $40\text{ ns} \pm 4\text{ ns}$, respectively.
- Duty cycle may be stretched/shrunk during speed changes or while transition to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.

2.9.3.4.2 SGMII Receive AC Timing Specifications

This table provides the SGMII receive AC timing specifications. Source synchronous clocking is not supported. Clock is recovered from the data. Figure 31 shows the SGMII Receiver Input Compliance Mask eye diagram.

Table 42. SGMII Receive AC Timing Specifications

At recommended operating conditions with $X2V_{DD} = 1.0V \pm 5\%$.

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Deterministic Jitter Tolerance	JD	0.37	—	—	UI p-p	1
Combined Deterministic and Random Jitter Tolerance	JDR	0.55	—	—	UI p-p	1
Sinusoidal Jitter Tolerance	JSIN	0.1	—	—	UI p-p	1
Total Jitter Tolerance	JT	0.65	—	—	UI p-p	1
Bit Error Ratio	BER	—	—	10^{-12}		—
Unit Interval	UI	799.92	800	800.08	ps	2
AC Coupling Capacitor	C_{TX}	5	—	200	nF	3

Notes:

1. Measured at receiver.
2. Each UI is 800 ps \pm 100 ppm.
3. The external AC coupling capacitor is required. It is recommended to be placed near the chip transmitter outputs.

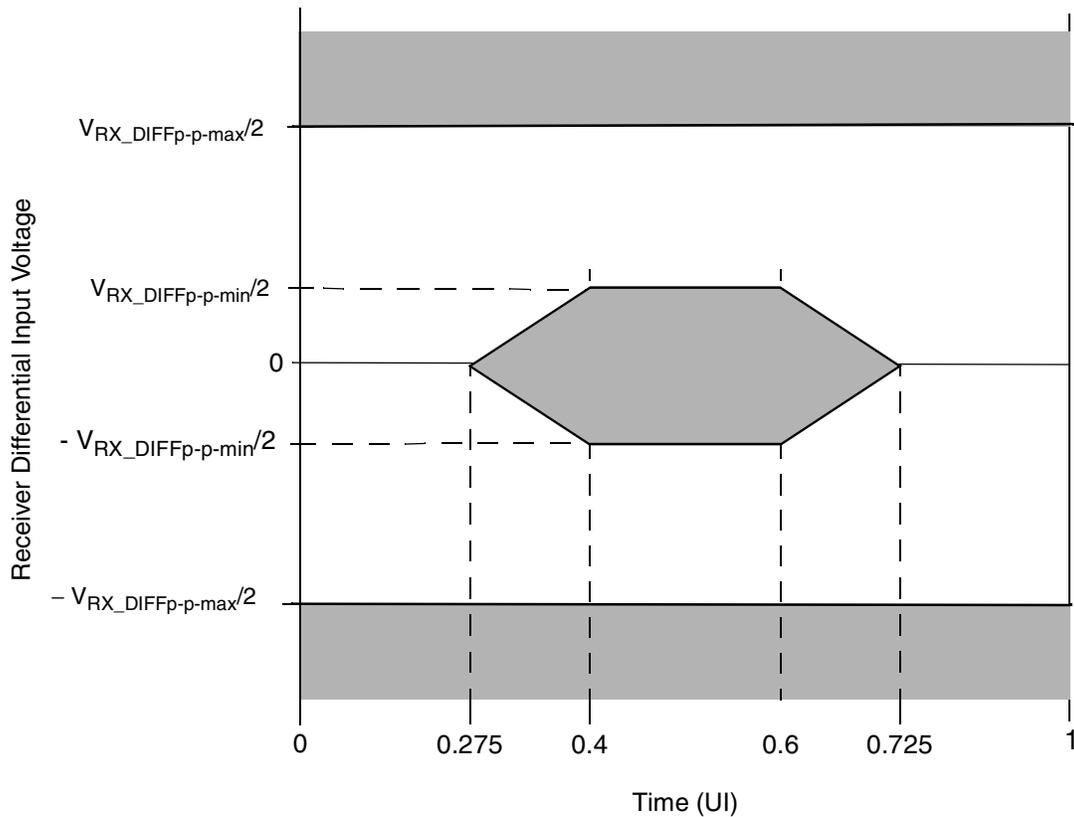


Figure 31. SGMII Receiver Input Compliance Mask

2.11.1 USB DC Electrical Characteristics

This table provides the DC electrical characteristics for the USB interface.

Table 46. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	-0.3	0.8	V
Input current	I_{IN}	—	± 5	μA
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V

Note:

1. The symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

2.11.2 USB AC Electrical Specifications

This table describes the general timing parameters of the USB interface of the chip.

Table 47. USB General Timing Parameters⁶

Parameter	Symbol ¹	Min	Max	Unit	Notes
usb clock cycle time	t_{USCK}	15	—	ns	2-5
Input setup to usb clock - all inputs	t_{USIVKH}	4	—	ns	2-5
input hold to usb clock - all inputs	t_{USIXKH}	1	—	ns	2-5
usb clock to output valid - all outputs	$t_{USKH OV}$	—	7	ns	2-5
Output hold from usb clock - all outputs	$t_{USKH OX}$	2	—	ns	2-5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(First\ two\ letters\ of\ functional\ block)(signal)(state)\ (reference)(state)}$ for inputs and $t_{(First\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{USIXKH} symbolizes usb timing (US) for the input (I) to go invalid (X) with respect to the time the usb clock reference (K) goes high (H). Also, $t_{USKH OX}$ symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.
6. When switching the data pins from outputs to inputs using the USBn_DIR pin, the output timings will be violated on that cycle because the output buffers are tristated asynchronously. This should not be a problem, because the PHY should not be functionally looking at these signals on that cycle as per ULPI specifications

Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 1.8$ V DC.

Table 50. Local Bus DC Electrical Characteristics (1.8 V DC)

Parameter	Symbol	Condition	Min	Max	Unit
Supply voltage 1.8V	BV_{DD}	—	1.71	1.89	V
High-level input voltage	V_{IH}	—	$0.65 \cdot BV_{DD}$	$0.3 + BV_{DD}$	V
Low-level input voltage	V_{IL}	—	-0.3	$0.35 \cdot BV_{DD}$	V
Input current ($BV_{IN}^1 = 0$ V or $BV_{IN} = BV_{DD}$)	I_{IN}	—	-15	10	μ A
High-level output voltage	V_{OH}	$I_{OH} = -100$ μ A	$BV_{DD} - 0.2$	—	V
		$I_{OH} = -2$ mA	$BV_{DD} - 0.45$	—	
Low-level output voltage	V_{OL}	$I_{OH} = 100$ μ A	—	0.2	V
		$I_{OH} = 2$ mA	—	0.45	

Note:

- Note that the symbol BV_{IN} , in this case, represents the BV_{IN} symbol referenced in [Table 1](#).

2.12.2 Local Bus AC Electrical Specifications

This table describes the general timing parameters of the local bus interface at $BV_{DD} = 3.3$ V DC. For information about the frequency range of local bus see [Section 2.23.1, “Clock Ranges.”](#)

Table 51. Local Bus General Timing Parameters ($BV_{DD} = 3.3$ V DC)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$		150	ps	7
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.3	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.4	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3

Table 51. Local Bus General Timing Parameters (BV_{DD} = 3.3 V DC) (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	t _{LBKHOX2}	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	t _{LBKHOZ1}	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ2}	—	2.5	ns	5

Note:

- The symbols used for timing specifications herein follow the pattern of t_{(First two letters of functional block)(signal)(state) (reference)(state)} for inputs and t_{(First two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
- All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
- All signals are measured from BV_{DD}/2 of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to 0.4 × BV_{DD} of the signal in question for 3.3-V signaling levels.
- Input timings are measured at the pin.
- For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
- Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV_{DD}/2.

This table describes the general timing parameters of the local bus interface at BV_{DD} = 2.5 V DC.

Table 52. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC)

Parameter	Configuration	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	—	t _{LBK}	7.5	12	ns	2
Local bus duty cycle	—	t _{LBKH} /t _{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	t _{LBKSKEW}	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	—	t _{LBIVKH1}	1.9	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	t _{LBIVKH2}	1.8	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	t _{LBIXKH1}	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	t _{LBIXKH2}	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	—	t _{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	—	t _{LBKHOV1}	—	2.4	ns	—
Local bus clock to data valid for LAD/LDP	—	t _{LBKHOV2}	—	2.5	ns	3
Local bus clock to address valid for LAD	—	t _{LBKHOV3}	—	2.4	ns	3
Local bus clock to LALE assertion	—	t _{LBKHOV4}	—	2.4	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	—	t _{LBKHOX1}	0.8	—	ns	3

Electrical Characteristics

Table 52. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC) (continued)

Parameter	Configuration	Symbol ¹	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	—	t _{LBKHOX2}	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	—	t _{LBKHOZ1}	—	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	—	t _{LBKHOZ2}	—	2.6	ns	5

Note:

- The symbols used for timing specifications herein follow the pattern of t_{(First two letters of functional block)(signal)(state) (reference)(state)} for inputs and t_{(First two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
- All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
- All signals are measured from BV_{DD}/2 of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to 0.4 × BV_{DD} of the signal in question for 2.5-V signaling levels.
- Input timings are measured at the pin.
- For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
- Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV_{DD}/2.

This table describes the general timing parameters of the local bus interface at BV_{DD} = 1.8 V DC.

Table 53. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC)

Parameter	Configuration	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	—	t _{LBK}	7.5	12	ns	2
Local bus duty cycle	—	t _{LBKH} /t _{LBK}	43	57	%	
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	t _{LBKSKEW}		150	ps	7
Input setup to local bus clock (except LUPWAIT)	—	t _{LBIVKH1}	2.4	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	t _{LBIVKH2}	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	t _{LBIXKH1}	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	t _{LBIXKH2}	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	—	t _{LBOTOT}	1.2	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	—	t _{LBKHOV1}	—	3.2	ns	—
Local bus clock to data valid for LAD/LDP	—	t _{LBKHOV2}	—	3.2	ns	3
Local bus clock to address valid for LAD	—	t _{LBKHOV3}	—	3.2	ns	3
Local bus clock to LALE assertion	—	t _{LBKHOV4}	—	3.2	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	—	t _{LBKHOX1}	0.9	—	ns	3

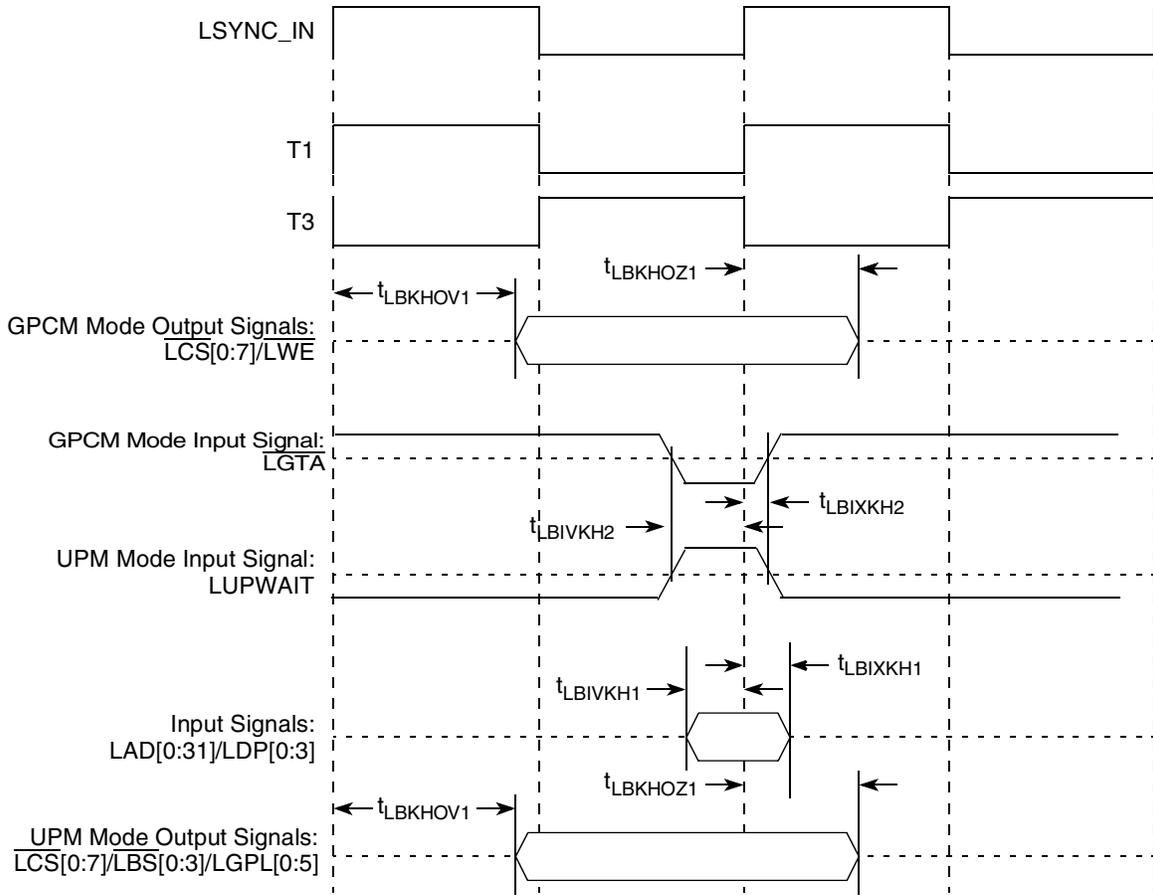


Figure 41. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4(PLL Enabled)

Table 63. I²C DC Electrical Characteristics (continued)

At recommended operating conditions with OV_{DD} of $3.3\text{ V} \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}(\text{max})$)	I_I	-10	10	μA	3
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. See the *MPC8536E PowerQUICC III Integrated Processor Reference Manual* for information on the digital filter used.
3. I/O pins will obstruct the SDA and SCL lines if OV_{DD} is switched off.

2.17.2 I²C AC Electrical Specifications

This table provides the AC timing parameters for the I²C interfaces.

Table 64. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see [Table 63](#)).

Parameter	Symbol ¹	Min	Max	Unit	Notes
SCL clock frequency	f_{I2C}	0	400	kHz	—
Low period of the SCL clock	t_{I2CL}	1.3	—	μs	—
High period of the SCL clock	t_{I2CH}	0.6	—	μs	—
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs	—
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs	—
Data setup time	t_{I2DVKH}	100	—	ns	—
Data hold time: CBUS compatible masters I ² C bus devices	t_{I2DXKL}	— 0	— —	μs	2
Data output delay time	t_{I2OVKL}	—	0.9	μs	3
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs	—
Rise time of both SDA and SCL signals	t_{I2CR}	—	300	ns	4
Fall time of both SDA and SCL signals	t_{I2CF}	—	300	ns	4

Table 79. Package Thermal Characteristics (continued)

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Junction-to-ambient (@200 ft/min)	Four layer board (2s2p)	R _{θJA}	14	°C/W	1, 2
Junction-to-board thermal	—	R _{θJB}	10	°C/W	3
Junction-to-case thermal	—	R _{θJC}	< 0.1	°C/W	4

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 and JESD51-6 with the board (JESD51-9) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the active surface of the die and the case top surface determined by the cold plate method (MIL SPEC-883 Method 1012.1) with the calculated case temperature. Actual thermal resistance is less than 0.1 °C/W

Simulations with heat sinks were done with the package mounted on the 2s2p thermal test board. The thermal interface material was a typical thermal grease such as Dow Corning 340 or Wakefield 120 grease. For system thermal modeling, the chip’s thermal model without a lid is shown in Figure 72. The substrate is modeled as a block 29 x 29 x 1.2 mm with an in-plane conductivity of 19.8 W/m•K and a through-plane conductivity of 1.13 W/m•K. The solder balls and air are modeled as a single block 29 x 29 x 0.5 mm with an in-plane conductivity of 0.034 W/m•K and a through plane conductivity of 12.1 W/m•K. The die is modeled as 9.6 x 9.57 mm with a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate assuming a conductivity of 7.5 W/m•K in the thickness dimension of 0.07 mm. The die is centered on the substrate. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

2.24.2 Recommended Thermal Model

This table shows the chip’s thermal model.

Table 80. Thermal Model

Conductivity	Value	Units
Die (9.6x9.6 × 0.85 mm)		
Silicon	Temperature dependent	—
Bump/Underfill (9.6 x 9.6 × 0.07 mm) Collapsed Thermal Resistance		
Kz	7.5	W/m•K
Substrate (29 × 29 × 1.2 mm)		
Kx	19.8	W/m•K
Ky	19.8	
Kz	1.13	
Solder and Air (29 × 29 × 0.5 mm)		
Kx	0.034	W/m•K
Ky	0.034	
Kz	12.1	

These capacitors should have a value of 0.1 μF . Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 μF (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values types and quantity of bulk capacitors.

3.5 SerDes Block Power Supply Decoupling Recommendations

The SerDes1 and SerDes2 blocks require a clean, tightly regulated source of power (SnV_{DD} and XnV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the chip. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the chip as close to the supply and ground connections as possible.
- Second, there should be a 1- μF ceramic chip capacitor from each SerDes supply (SnV_{DD} and XnV_{DD}) to the board ground plane on each side of the chip. This should be done for all SerDes supplies.
- Third, between the chip and any SerDes voltage regulator there should be a 10- μF , low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100- μF , low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

3.6 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs should be tied to V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} as required. All unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} and GND pins of the chip.

3.7 Pull-Up and Pull-Down Resistor Requirements

The chip requires weak pull-up resistors (2–10 k Ω is recommended) on open drain type pins including I²C pins and MPIC interrupt pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in [Figure 78](#). Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

The following pins must NOT be pulled down during power-on reset: TSEC1_TXD[3], HRESET_REQ, TRIG_OUT/READY/QUIESCE, MSRCID[2:4], ASLEEP. The UART_SOUT[0:1] and TEST_SEL pins must be set to a proper state during POR configuration. Please refer to the pinlist table (see [Table 62](#)) of the individual chip for more details.

See the PCI 2.2 specification for all pull-ups required for PCI.

3.8 Output Buffer DC Impedance

The chip drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I²C).

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio and e500 PLL ratio configuration pins are not equipped with these default pull-up devices.

3.10 JTAG Configuration Signals

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in [Figure 78](#). Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

Boundary-scan testing is enabled through the JTAG interface signals. The $\overline{\text{TRST}}$ signal is optional in the IEEE 1149.1 specification, but it is provided on all processors built on Power Architecture technology. The chip requires $\overline{\text{TRST}}$ to be asserted during power-on reset flow to ensure that the JTAG boundary logic does not interfere with normal chip operation. While the TAP controller can be forced to the reset state using only the TCK and TMS signals, generally systems assert $\overline{\text{TRST}}$ during the power-on reset flow. Simply tying $\overline{\text{TRST}}$ to $\overline{\text{HRESET}}$ is not practical because the JTAG interface is also used for accessing the common on-chip processor (COP), which implements the debug interface to the chip.

The COP function of these processors allow a remote computer system (typically, a PC with dedicated hardware and debugging software) to access and control the internal operations of the processor. The COP interface connects primarily through the JTAG port of the processor, with some additional status monitoring signals. The COP port requires the ability to independently assert $\overline{\text{HRESET}}$ or $\overline{\text{TRST}}$ in order to fully control the processor. If the target system has independent reset sources, such as voltage monitors, watchdog timers, power supply failures, or push-button switches, then the COP reset signals must be merged into these signals with logic.

The arrangement shown in [Figure 78](#) allows the COP port to independently assert $\overline{\text{HRESET}}$ or $\overline{\text{TRST}}$, while ensuring that the target can drive $\overline{\text{HRESET}}$ as well.

The COP interface has a standard header, shown in [Figure 79](#), for connection to the target system, and is based on the 0.025" square-post, 0.100" centered header assembly (often called a Berg header). The connector typically has pin 14 removed as a connector key.

The COP header adds many benefits such as breakpoints, watchpoints, register and memory examination/modification, and other standard debugger features. An inexpensive option can be to leave the COP header unpopulated until needed.

There is no standardized way to number the COP header; consequently, many different pin numbers have been observed from emulator vendors. Some are numbered top-to-bottom then left-to-right, while others use left-to-right then top-to-bottom, while still others number the pins counter clockwise from pin 1 (as with an IC). Regardless of the numbering, the signal placement recommended in [Figure 79](#) is common to all known emulators.

3.10.1 Termination of Unused Signals

If the JTAG interface and COP header will not be used, Freescale recommends the following connections:

- $\overline{\text{TRST}}$ should be tied to $\overline{\text{HRESET}}$ through a 0 k Ω isolation resistor so that it is asserted when the system reset signal ($\overline{\text{HRESET}}$) is asserted, ensuring that the JTAG scan chain is initialized during the power-on reset flow. Freescale recommends that the COP header be designed into the system as shown in [Figure 78](#). If this is not possible, the isolation resistor will allow future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.
- No pull-up/pull-down is required for TDI, TMS, or TDO.

5. Capacitors may not be present on all devices
6. Caution must be taken not to short exposed metal capacitor pads on package top.
7. All dimensions are symmetric across the package center lines, unless dimensioned otherwise.

6 Product Documentation

The following documents are required for a complete description of the chip and are needed to design properly with the part.

- *MPC8536E PowerQUICC III Integrated Processor Reference Manual* (document number: MPC8536ERM)
- *e500 PowerPC Core Reference Manual* (document number: E500CORERM)

7 Document Revision History

This table provides a revision history for this hardware specification.

Table 85. Document Revision History

Revision	Date	Substantive Change(s)
5	09/2011	<ul style="list-style-type: none"> • Removed PVDD from Table 1, "Pinout Listing."
4	06/2011	<ul style="list-style-type: none"> • In Table 1, "Pinout Listing," updated the power supply for TSEC3 pins to TVDD. • Updated Table 56, "eSDHC AC Timing Specifications." • In Section 4.3, "Part Numbering," added an extra bin (1250/500/667) to support DDR3.
3	11/2010	<ul style="list-style-type: none"> • In Table 1, "Pinout Listing," added the following note: "For systems that boot from Local Bus (GPCM)-controlled NOR flash or (FCM) controlled NAND flash, a pullup on LGPL4 is required..." In addition, updated footnote 26 and added footnote 29 to PCI1_AD. • Updated Table 21 • Updated Figure 25, "RGMII and RTBI AC Timing and Multiplexing Diagrams." • In Table 44, "MII Management DC Electrical Characteristics," changed the Voh/Vol values for MDIO/MDC. • Added Note 6 regarding USBn_DIR pin to Table 47, "USB General Timing Parameters6." • In Table 64, "I2C AC Electrical Specifications," updated footnote 2. • In Table 82, Table 83, Table 84, added the Revision Level A for Rev 1.2
2	09/2009	<p>Note:</p> <ul style="list-style-type: none"> • In Section 1, "Pin Assignments and Reset States," updated the first sentence of the note to say, "The UART_SOUT[0:1] and TEST_SEL pins must be set to a proper state during POR configuration." • In Table 40, "SGMII DC Receiver Electrical Characteristics," changed LSTSAB to LSTSA and LSTSEF to LSTSE for Note 4. • Updated Die value and Bump/Underfill value in Table 84 <p>Note: Updated Figure 81, "Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA," and its notes.</p>
1	09/2009	<ul style="list-style-type: none"> • In Table 3, "Recommended Operating Conditions," for V_{DD_CORE}, removed 1.1 ± 55 mV. • In Table 5, "Power Dissipation 5," remove note 5. • In Table 5, "Power Dissipation 5," changed an "—" to "0."
0	08/2009	<ul style="list-style-type: none"> • Initial public release.